

# WP4: Radiation Hard Semiconductor Detectors

## - Status of activities -

Michael Moll (PH-DT)

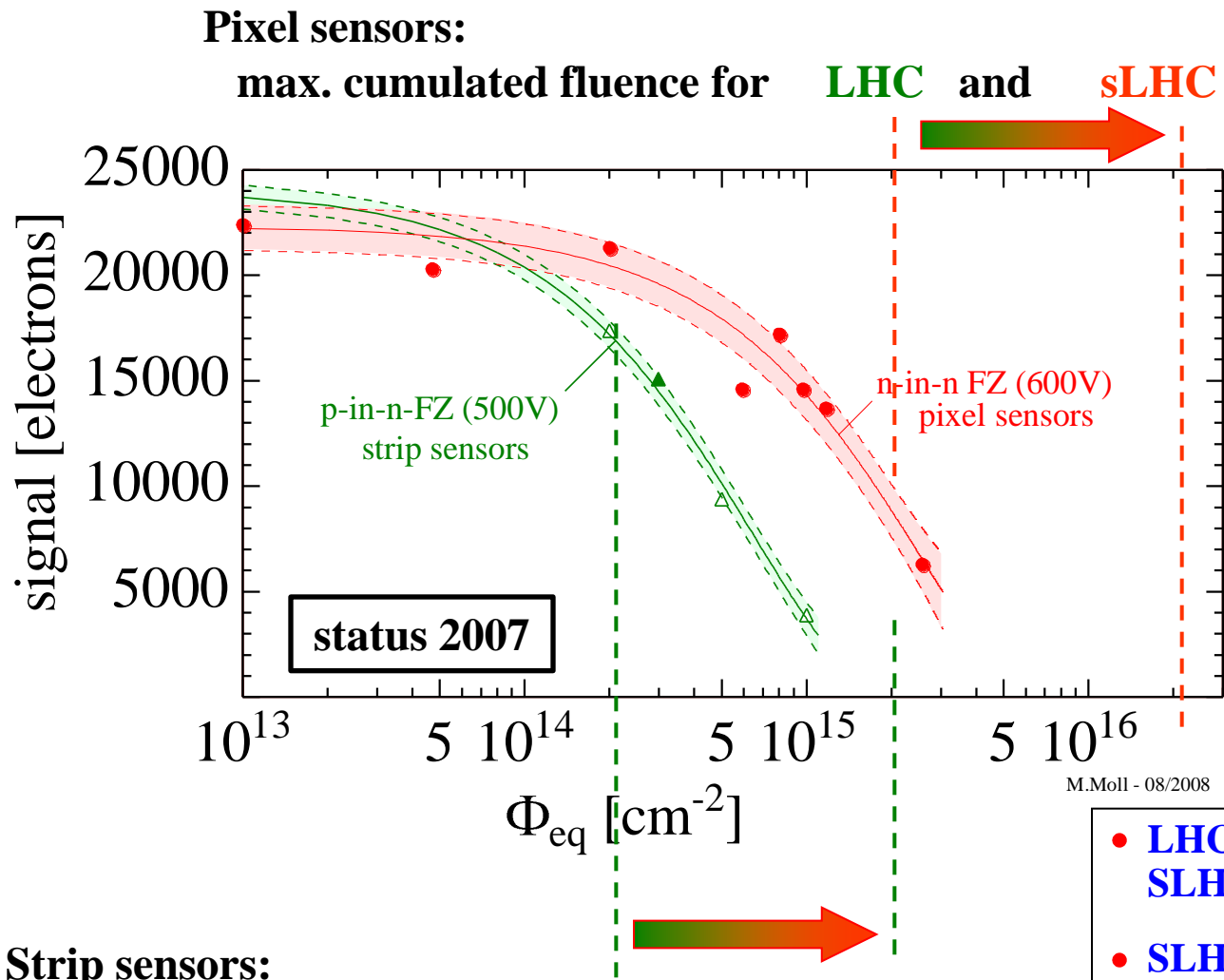
## OUTLINE

- **WP4 – Challenge and Aim**
- **WP4 – Work program, organization and participants**
- **Status:**
  - **Pixel sensor evaluation/development** (*in collaboration with ATLAS*)
  - **Strip sensor evaluation/development** (*in collaboration with CMS*)
  - **Generic R&D** (*in collaboration with RD50*)
  - **Build up of infrastructure** (*common CERN infrastructure*)
- **Work plan for 2010/2011**

# Challenge: Sensors for the sLHC Trackers



**Note:** Measured partly under different conditions!  
Lines to guide the eye (no modeling)!



FZ Silicon Strip and Pixel Sensors

- n-in-n (FZ), 285μm, 600V, 23 GeV p
- ▲ p-in-n (FZ), 300μm, 500V, 23GeV p
- △ p-in-n (FZ), 300μm, 500V, neutrons

References:

- [1] p/n-FZ, 300μm, (-30°C, 25ns), strip [Casse 2008]
- [2] n/n-FZ, 285μm, (-10°C, 40ns), pixel [Rohe et al. 2005]

- **LHC detectors would fail in SLHC due to radiation damage**
- **SLHC will need more radiation tolerant tracking detector concepts!**

## WP4 is organized around 4 partly overlapping projects

- **1. Development and evaluation of pixel sensor concepts**  
in framework of ATLAS Pixel Upgrade projects (H.Pernegger)
  - Evaluation of rad. tolerant sensors for innermost pixel layers in view of IBL and sLHC pixel:  
**Pixel technologies: Silicon planar sensors, Silicon 3D sensors, Diamond sensors**
  - Support in organizing and running of testbeam and irradiation campaigns for the ATLAS pixel community.
- **2. Development and evaluation of sensor concepts for CMS upgrade**  
in framework of CMS Tracker upgrade projects (A.Peisert (since 2010), M.Mannelli (before))
  - Sensor R&D program with HPK (Hamamatsu) to evaluate sensors based on various silicon **sensor materials: FZ, MCZ and EPI silicon of n- and p-type and different thickness**
  - Part of prg. for preproduction, qualification and large scale production of CMS phase II upgrade
- **3. Generic R&D on radiation tolerance of silicon sensors**  
in framework of RD50 project (M.Moll)
  - Generic R&D on understanding of radiation damage in silicon
- **4. Build up of test equipment & infrastructure for PH common use (M.Moll)**
  - Equipment: Probestations for CV/IV measurements of sensors
  - TCT/  $\beta$ -source test system in climate controlled container
  - Offer services as part of PH Departmental Silicon Facility

# WP4 – Participants

**Challenge:** make WP4 a common activity with long term profit for CERN-PH

**ATLAS**

**CMS**

**RD50**

**PH-DT ssd support to all CERN Experiments**

**Coordinator:** **Michael Moll (PH-DT)**

**Project 1 (ATLAS - Pixel):**

- **WP4-Fellow:** **Alessandro La Rosa**; **WP4-PhD:** **Christian Gallrapp**
- **Daniel Dobos, Heinz Pernegger**, (*B.di Girolamo, F.Dittus*)

**Project 2 (CMS - Tracker):**

- **A.Peisert, M.Mannelli, S.Mersi, student Joyeeta Sinha (4 months), Georg Auzinger (PhD)**, (*Duccio Abbaneo*)
- **Technical support** (*1.3 FTE: J.F. Pernot, J.P. Chatelain, E. Albert, H. Postema, A. Tsirou, I. Ahmed*)

Note: Tech support also given to Project 3&4

**Project 3 & 4 (RD50 & ssd test equipment):**

- **WP4-Fellows:** **Manuel Fahrer , Irena Dolenc**
- **M.Moll, N.Pacifico (MCPAD ESR), E.Castillo Sanchez (Trainee)**
- **R.Fortin, DT-FSU (Technical support)**

Note: Participation also in Project 2

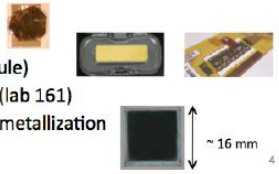
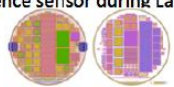
**Observers (presently no active role)**

- **LHCb :** **Paula Collins**
- **ALICE :** **Petra Riedler**
- **TOTEM:** **Gennaro Ruggiero**

- **Interest:** performance evaluation of different sensors type for LHC phase 1 ( in particular ATLAS IBL) and phase 2 upgrade with LHC and SLHC electronics (characterization before & after irradiation)

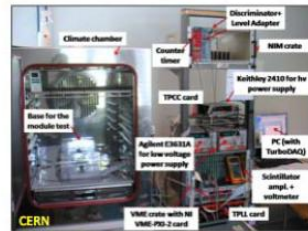
- **Available device for characterization:**

- **ATLAS Planar**
  - N-in-N from Pixel production (used as reference sensor during Lab, irradi. and beam tests)
  - N-in-N and N-in-P from CiS (expected soon)
- **ATLAS 3D-Si**
  - Double side double type column from FBK-irst
  - Passing-Through-Column (FE-I3 compatible) from FBK-irst (end spring)
  - Passing-Through-Column from Common floor-plan (from all vendors) (FE-I3 and FE-I4)(expected in early summer)
- **ATLAS Diamond**
  - 1x Irradiated scCVD (single-chip / FE-I3)
  - 3x unirrad. and 1x irradi. pCVD (full module)
  - 3x scCVD (single-chip / FE-I3) under test (lab 161)
  - 2x pCVD (single-chip / FE-I4) in Bonn for metallization

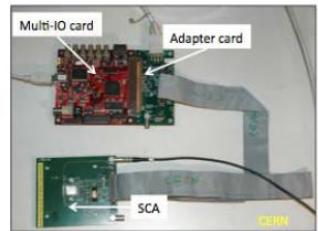


WP4 Status Report, 6.4.2010 - Alessandro La Rosa (CERN-DT)

- **ATLAS FE-Ix Experimental set up:**



ATLAS – TurboDAQ (FE-I3)  
TPLL and TPCC  
VME based



ATLAS – USBPix (FE-I3 and FE-I4 chips)  
USB based



WP4 Status Report, 6.4.2010 - Alessandro La Rosa (CERN-DT)

Setups available in Lab 161-01-24

- **Activities:**

- Lab measurements (electrical test, threshold & noise and response to radioactive source tests)
- Test beam at CERN SPS (hit eff., pulse high distribution, charge sharing and residual distr.)
- Common irradiation at CERN PS
- Post-irrad. validation (Electrical & Lab characterization + Test beam measurements)

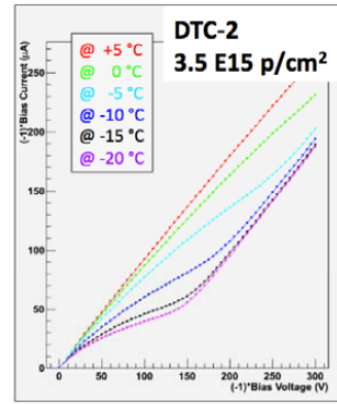
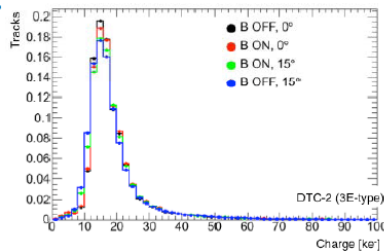
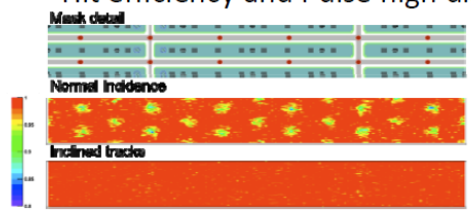
- Silicon (FBK: 3D-Si, dtc type)

- Lab measurements

- IV study shows a breakdown about 70 V
    - Sr90 source test → good CCE and less charge sharing than planar

- Testbeam measurements

- DUTs tested w/ & w/out 1.6T magnetic field and at 0° and 15° of beam angle of incidence
    - Hit efficiency and Pulse high dist.



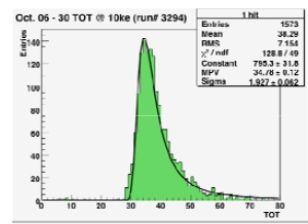
- Irradiation

- First test after 3.5 e15 p/cm² → Behavior in agreement with theory:
      - Low temperature low current
      - Damage rate:  $\alpha(1.24 \text{ e}15 \text{ n}_{\text{eq}}/\text{cm}^2)=4 \text{ e-}17$  and  $\alpha(2.17 \text{ e}15 \text{ e}15 \text{ n}_{\text{eq}}/\text{cm}^2) = 5 \text{ e-}17$

- Diamond

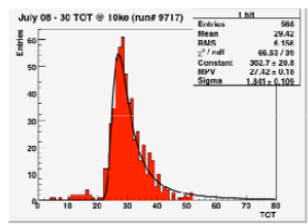
- Lower capacitance → Lower Th (fact. 2) & Noise but ~50% of collected signal
  - “invisible” if compared w/ bare FE
  - Before & after irradi study

**BEFORE irradiation**



MPV=35

**AFTER irradi (7 e14 p/cm²)**



MPV=27 (79% of unirrad)



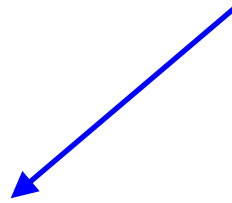
**Project is integral part of CMS Tracker upgrade**

**WP4 participation in Phase I:**

- coordination of project: F.Hartmann  
M .Mannelli (HPK contact)  
A. Peisert (coord meas. at CERN)
- irradiation of sensors
- characterization of sensors  
(... requires still set up of some specific equipment at CERN)

**Outline plan:**

- **Phase I: Targeted R&D**
  - Establish required sensors characteristics & basic specifications
  - Single Source R&D with HPK agreed with CERN, together with framework for Market Survey & Procurements for Phase II & Phase III
- **Phase II: Preproduction and Qualification**
  - Finalize detailed specifications and QA protocols
  - Qualify for large scale production
- **Phase III: Large Scale Production**



- **Aim: Identify technology for tracker upgrade**
- **Delivery of sensors expected in June 2010**
  - **Different silicon material, different technologies**

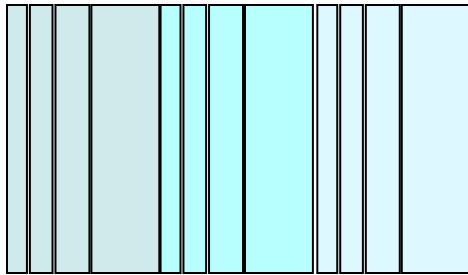
substrate type & Active Thickness	FZ 200um carrier	MCZ 200um thinning	FZ 100um carrier	epi 100um	epi 75um	FZ 300um	Total
P-on-N Production	6	6	6	6	6	6	36
N-on-P Production p-spray	6	6	6	6	6	6	36
N-on-P Production p-stop	6	6	6	6	6	6	36
2'nd metal production P-on-N	6						6
2'nd metal production N-on-P p-stop	6						6
2'nd metal production N-on-P p-spray	6						6
<b>Total</b>	<b>36</b>	<b>18</b>	<b>18</b>	<b>18</b>	<b>18</b>	<b>18</b>	<b>126</b>

- **Evaluate**
  - **Geometry**
  - **Radiation hardness and annealing behavior**



- Each wafer contains ~ 30 different sensors and test structures
- Massive irradiation and test campaign organized
- CERN will participate in evaluation of

- A) multi-geometry strip and pixel detectors (*A.Peisert et al.*)



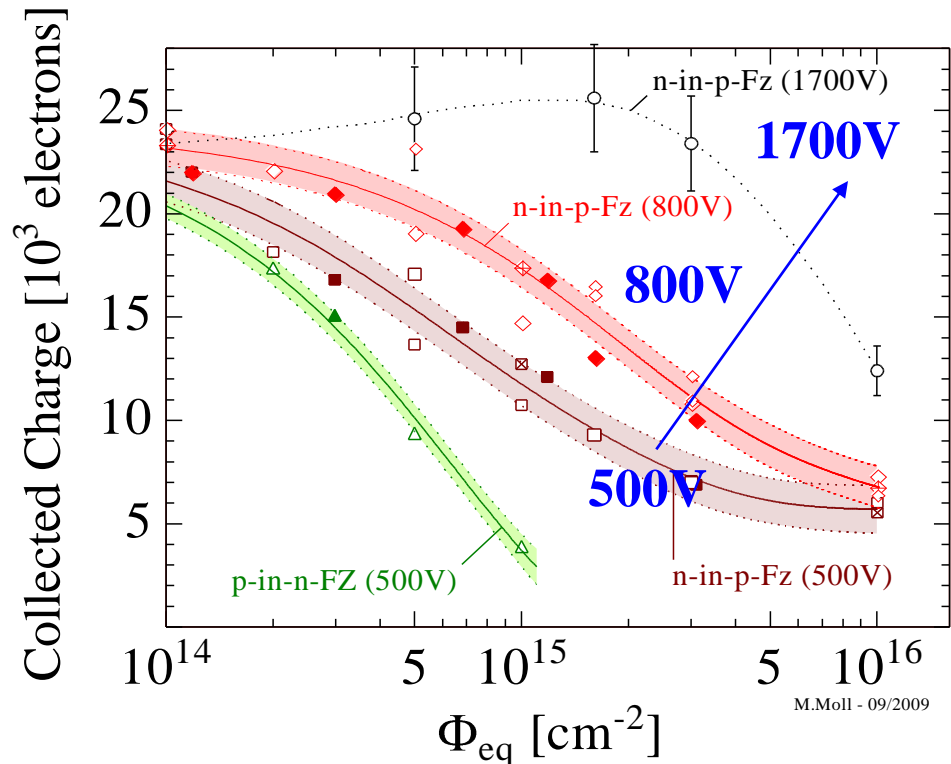
3 regions, 4 groups of 32 strips in each region  
 pitch 70  $\mu\text{m}$ , 80  $\mu\text{m}$ , 240  $\mu\text{m}$ , 120  $\mu\text{m}$   
 different width/pitch in each region  
 ~3 cm long strips

Electrical tests: IV, CV,  $C_{\text{interstrip}}$ ,  $R_{\text{interstrip}}$ ,  $C_{\text{coupling}}$

Cosmic rack and x-y table for measurements with a source:  
 CCE, noise, position resolution

- B) pad diode test structures (*M.Moll et al.*)
  - CV, IV, CCE measurements, annealing studies
- Setups for measurements have to be ready in June

- **RD50 collaboration: 47 Institutions with 250 members**
- **WP4 involvement in management of collaboration** (*M.Moll co-spokesperson*)
- **CERN (WP4) R&D focused on RD50 key questions:**
  - **p-type silicon and its annealing behavior** (*'base line option'* for ATLAS Tracker upgrade)
  - **charge multiplication in highly irradiated sensors**
  - **radiation tolerance of p-in-n Magnetic Czochralski silicon sensors**



### FZ Silicon Strip Sensors

- n-in-p (FZ), 300μm, 500V, 23GeV p [1]
- n-in-p (FZ), 300μm, 500V, neutrons [1,2]
- ⊗ n-in-p (FZ), 300μm, 500V, 26MeV p [1]
- ◆ n-in-p (FZ), 300μm, 800V, 23GeV p [1]
- ◇ n-in-p (FZ), 300μm, 800V, neutrons [1,2]
- ◊ n-in-p (FZ), 300μm, 800V, 26MeV p [1]
- n-in-p (FZ), 300μm, 1700V, neutrons [2]
- ▲ p-in-n (FZ), 300μm, 500V, 23GeV p [1]
- △ p-in-n (FZ), 300μm, 500V, neutrons [1]

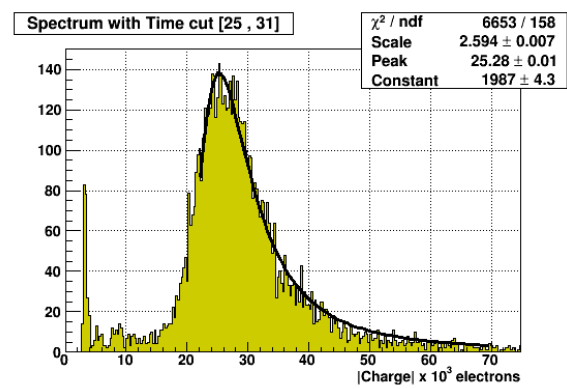
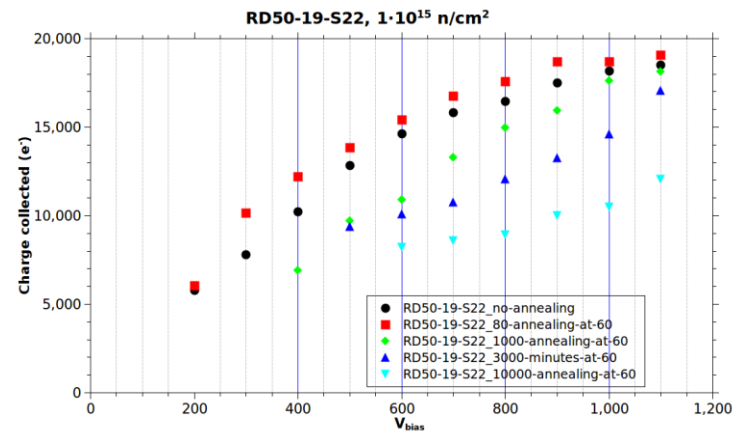
#### References:

- [1] G.Casse, VERTEX 2008 (p/n-FZ, 300μm, (-30°C, 25ns)
- [2] I.Mandic et al., NIMA 603 (2009) 263 (p-FZ, 300μm, -20°C to -40°C, 25ns)

M.Moll - 09/2009

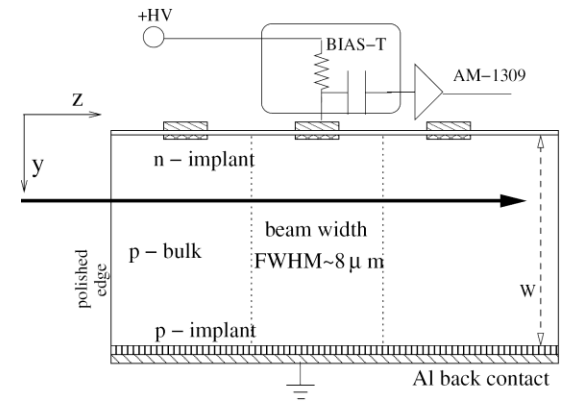
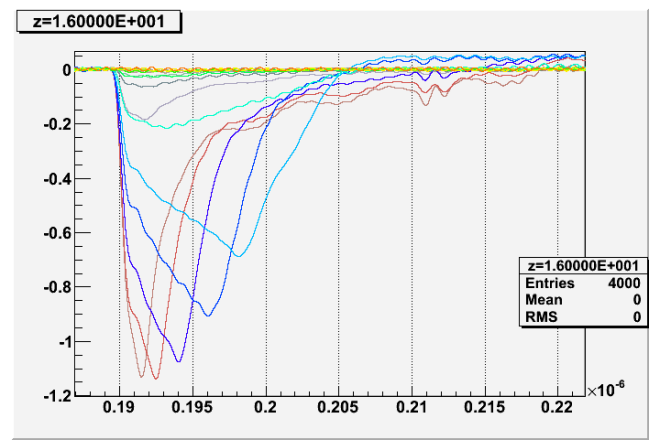
## Characterization of irradiated ministrip sensors

- **Annealing study on irradiated MCZ silicon strip sensors**
  - CCE with beta source and LHCb Beetle chip based DAQ (ALIBAVA)



## Characterization of charge transport inside irradiated sensors

- Edge TCT (Transient Charge Technique) with infrared picosecond laser



## # Solid State Detector Lab (SSD) in bldg.28 (attached to Silicon Facility – 186)

- **‘Refurbishment’ of ssd characterization tools**
  - Probe station for CV/IV measurements (4” chuck in dark box, CV/IV up to 1000V)
  - CCE with Sr<sup>90</sup> source (one channel,  $\mu$ s shaping, cooling)
  - Status: *Done, including centralized data storage and database*
- **New TCT(Transient Charge Technique)/CCE setup in bldg.28**
  - Status: *Done, see next slide (cooling needs to be improved to reach -40°C)*
- **New edge TCT system in bldg.28**
  - Status: *first measurements done, needs further work*

## # ATLAS Pixel laboratory (bldg. 161)

- **Pixel test stations in Bat 161 for sensor + FE chip measurements**
  - Status: *Fully operational; With source and electronic calibration in climate chamber*

## # Silicon Facility – bldg 186

- **New 4 inch probe station with cold chuck for CV/IV measurements**
  - Status: *Almost ready, delay due to work load of technicians in other projects*
- **Cold box installation for measuring CMS multistrip geometry sensors**
  - Status: *Will be ready in June for arrival of first HPK sensors*

## Characterization methods

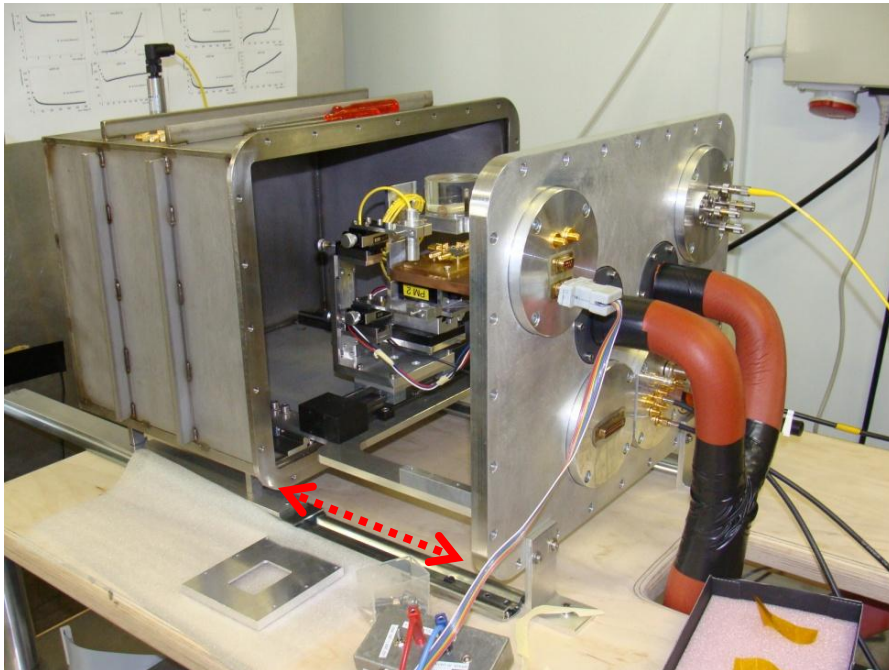
- **TCT (Transient Charge Technique)**
  - strip and pad sensors, multichannel
  - lasers illumination on both sides of sample
  - red + infrared laser (ps pulses)
- **CCE (Charge collection efficiency)**
  - Sr<sup>90</sup> source
  - Scintillator based trigger
- **CV / IV**
  - CV with frequency up to 1 MHz

## Mechanics & Cooling

- **Cooled with silicon oil**
  - vacuum or dry air atmosphere
  - Temperatures down to below -25°C  
(down to -40° C with peltier booster)
- **Movable with linear motor stage**
  - laser and source  
can be scanned over DUT
- **Modular system with flanges**
  - allows for easy mounting of additional  
feedthroughs

## Sample mounting & Electronics

- **SMA connectors (HF)**
  - 2.5 GHz oscilloscope (epool)
- **Sample boards (support PCB)**
  - detectors to be bonded
  - good thermal & HF properties
- **Amplification**
  - Fast commercial amplifiers
  - ALIBAVA system for strip sensor CCE
    - based on LHCb Beetle Chip
    - 25ns shaping time, 128 channels



### Comment from Heinz Pernegger:

- **Two major areas of contributions for ATLAS IBL and sLHC upgrade**
  - IBL Pixel Sensor Development interrelates with WP project on sensors
  - IBL Integration and stave studies interrelates with WP project on cooling (CO<sub>2</sub>)
- **People currently involved:**
  - D. Dobos, F. Dittus, C. Gallrapp, A. La Rosa, H. Pernegger
  - M. Capeans, A. Catinaccio
  - Work carried out in close cooperation between PH-ADE, PH-ADO and PH-DT
- **Pixel Sensor Development for IBL and sLHC**
  - Planar, 3D silicon and CVD diamond pixel sensors
    - Studies of irradiated pixel detectors in Lab
  - Major responsibility for Irradiation and Testbeams
    - Coordinator for IBL and 3D irradiation (A. La Rosa)
  - We have setup and operate facility for pixel tests in Bat 161 which is used by whole collaboration
- **Significant contribution to the ongoing IBL module development program:**
  - Module prototype program (tests of sensor-chip assemblies)
  - Tests of new FEI4 pixel chip for IBL (module test analysis, DAQ)
  - Major partners: Bonn, Ohio, Genova/Trento, Dortmund

### Comment from Heinz Pernegger:

*The cooperation between WP4 and ATLAS pixel sensor development has been very successful and beneficial for both*

- **The generic sensor development benefit strongly from experiment developments (e.g. availability of pixel electronics)**
- **For ATLAS, in particular the IBL, it allowed to support the development and evaluation of pixel sensors of different technologies**

*Specific support made possible through WP & Atlas cooperation on sensors*

- **Participation in sensor prototyping runs and manufacturing of evaluation prototypes**
  - **3D sensor development at FBK-irst for double sided and active-edge 3D sensors, optimization of design charge collection and noise performance**
  - **Planar sensor development for new n-n planar sensors at CIS with slim edges and improved radiation hardness**
  - **pCVD and scCVD diamond sensors for charge collection studies and diamond pixel module tests**
  - **Pixel bump-bonding to sensors at IZM**
- **Infrastructure**
  - **Update and improvement of sensor characterization lab in Bat 161**
  - **acquisition and further development of new readout electronics**
- **Support of personnel**
  - **Currently support one fellow (A. La Rosa) and one doctoral student (C. Gallrapp) through WP funds.**

**Comment from Duccio Abbaneo:**

**CMS silicon sensors R&D relies on WP4 and collaboration with the group of M. Moll**

- **Results from RD50 are the basis of the R&D program**
- **Access to DSF facilities and expertise**
- **CERN financial contribution to the project comes from WP4 funds**

**As soon as CMS has developed a well-structured R&D project, WP4 resources have been made available to the project (with a fair share with the other experiments). Without that, CERN participation in the project would not have been possible.**

**Thanks to this policy, WP4 resources are being used in the most effective way, without any barrier between “generic R&D” and “detector-specific R&D”.**

**In few words: fully useful WP, managed in an exemplary way.**



**Budget allocation 2010: 340 KCHF**

**CET: 155KCHF from  
2009 commitment on  
34004 not balanced yet !**

## Splitting on activities in 2010:

- |   |         |
|---|---------|
| • ATLAS activities                                | 65 KCHF |
| • CMS activities                                  | 65 KCHF |
| • RD50 activities                                 | 65 KCHF |
| • Infrastructure (common setups)                  | 65 KCHF |
| • PhD student, FSU, Fellow, epool, travel, others | 80 KCHF |



- **Workplan “ATLAS pixels”:**

- Test of sensor assemblies with new FEI4 chip (for IBL and sLHC)
- Characterization of irradiated sensors (planar, 3D and diamond)
- Organize and support common irradiations and test beams for ATLAS Pixel community
- Performance studies of pixel sensors for phase I upgrade (IBL)

- **Workplan “sensors for CMS”**

- Participate in CMS work on HPK sensor characterization before & after irradiation with main focus on multistrip structures and diodes/ministrip sensors

- **Workplan on activities in framework of RD50**

- Submission of detector production runs at Micron (2010)
- Detailed studies on reverse annealing in p-type silicon strip sensors
- Sensor characterizations with new infrastructure (fast/multi and edge TCT, Alibava)
- Start project on simulation of irradiated silicon sensors using commercial software

- **Workplan on common infrastructure at CERN**

- Produce second setup for CCE measurements with LHCb Beetle chip (ALIBAVA)
- Finalization of cold chuck system for CV/IV measurements